

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
80V	17mΩ @ V _{GS} = 10V	53.7A
	23.5mΩ @ V _{GS} = 4.5V	44.3A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

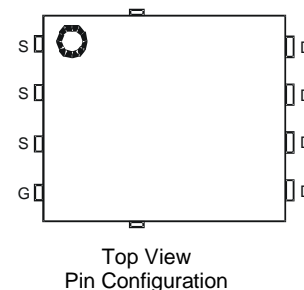
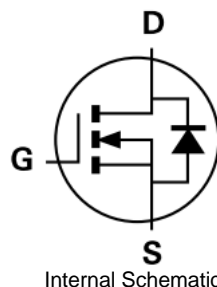
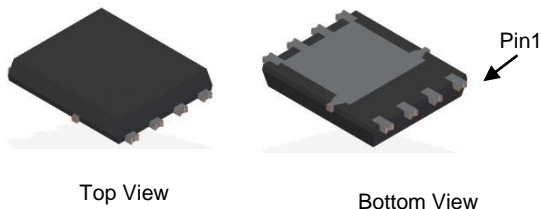
Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Additional Tin-plated on Sidewall Pads for Optical Solder Inspection
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: PowerDI[®] 5060-8 (SWP) (Type Q)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

PowerDI5060-8 (SWP) (Type Q)

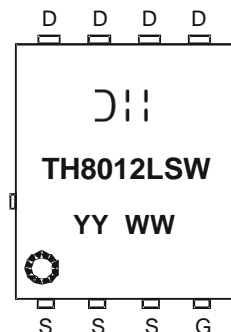


Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH8012LPSW-13	PowerDI5060-8 (SWP) (Type Q)	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



☺ = Manufacturer's Marking
 TH8012LSW = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 17 = 2017)
 WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	80	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 5)	I_D	$T_A = +25^\circ\text{C}$	10.3
		$T_A = +100^\circ\text{C}$	7.3
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	I_D	$T_C = +25^\circ\text{C}$	53.7
		$T_C = +100^\circ\text{C}$	38
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	80	A
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	69	A
Pulsed Body Diode Forward Current (10 μs Pulse, Duty Cycle = 1%)	I_{SM}	80	A
Avalanche Current, $L=0.1\text{mH}$	I_{AS}	11.6	A
Avalanche Energy, $L=0.1\text{mH}$	E_{AS}	6.7	mJ

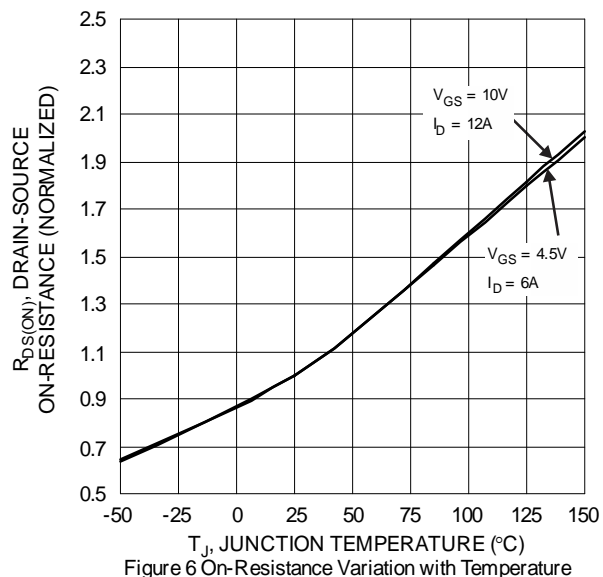
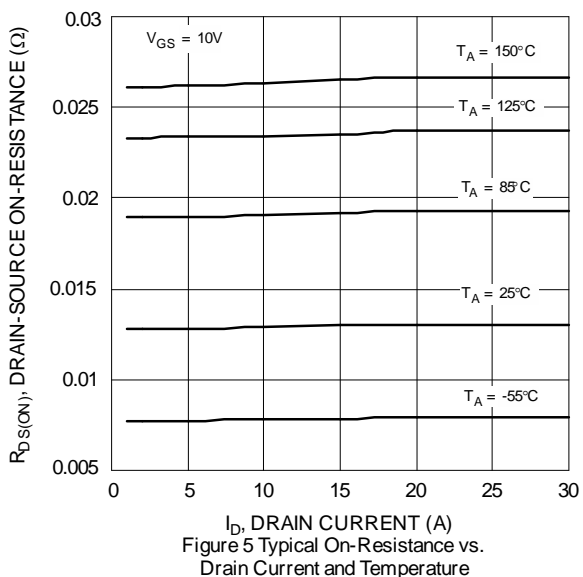
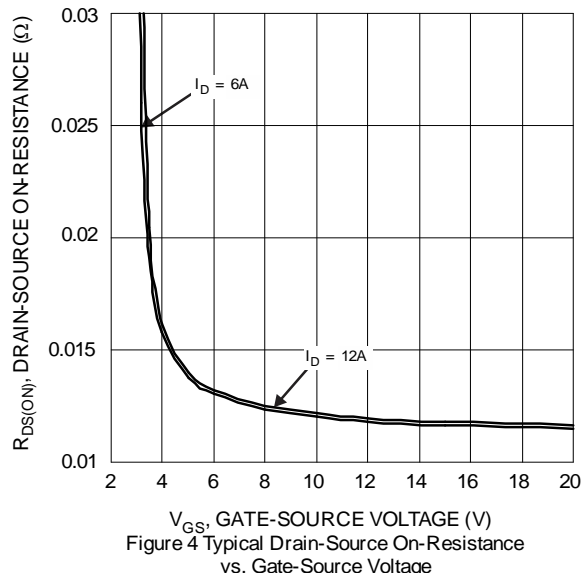
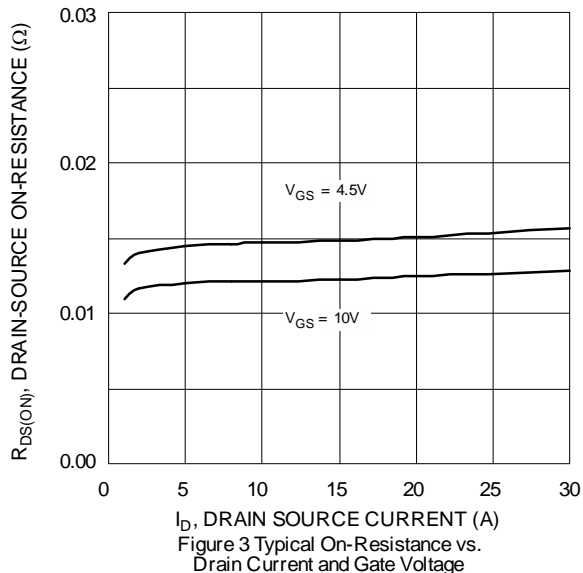
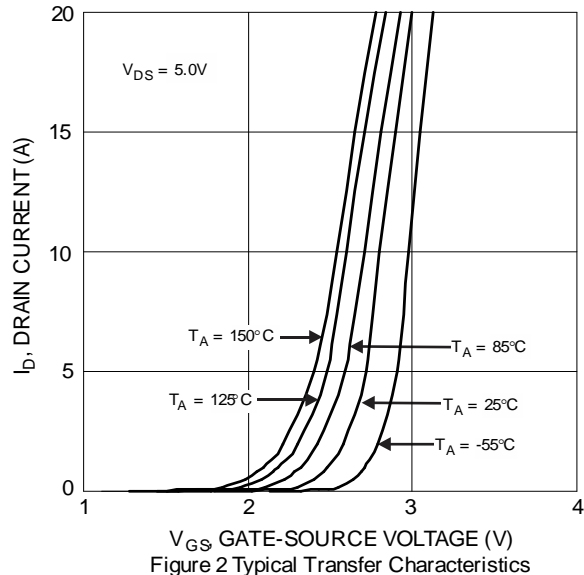
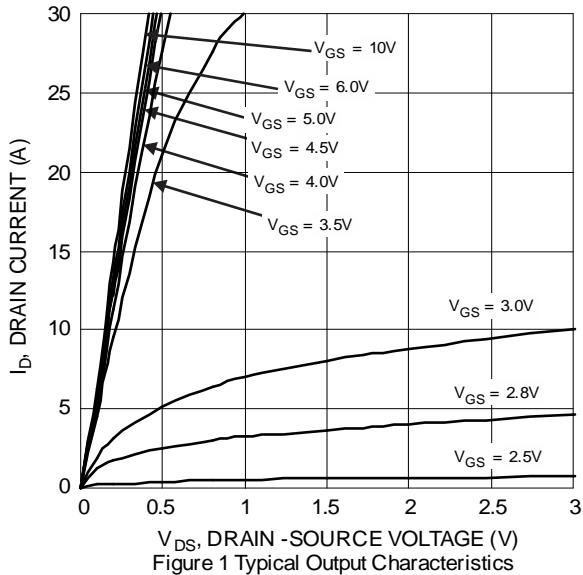
Thermal Characteristics

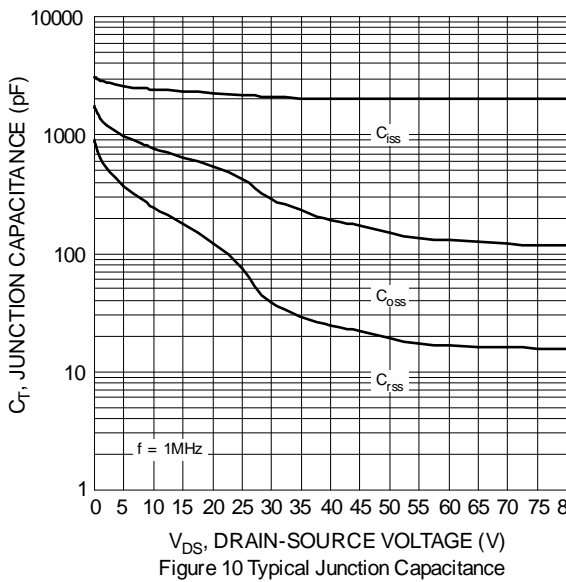
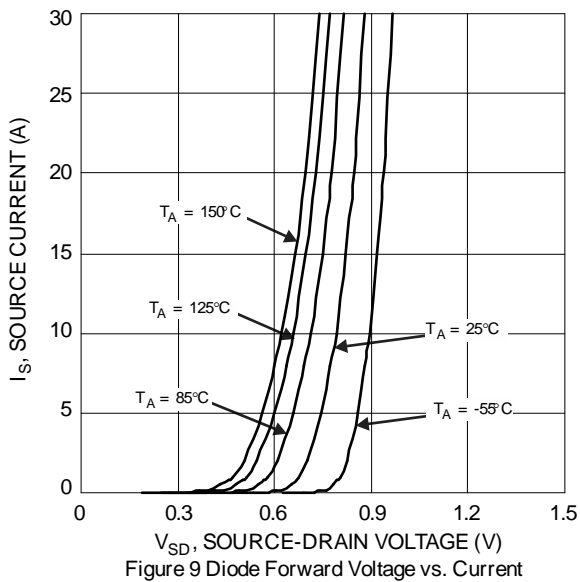
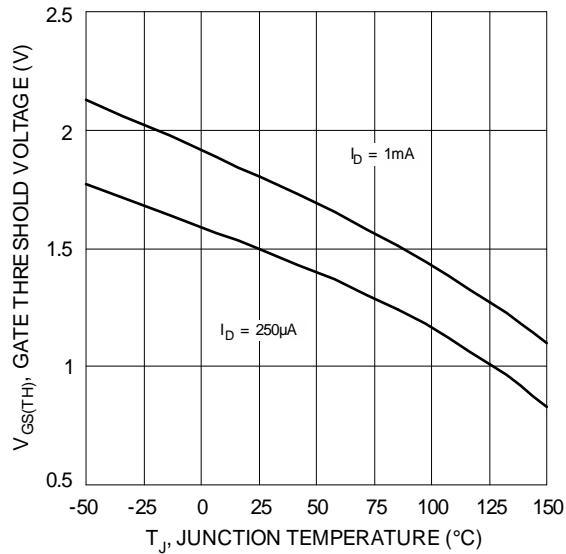
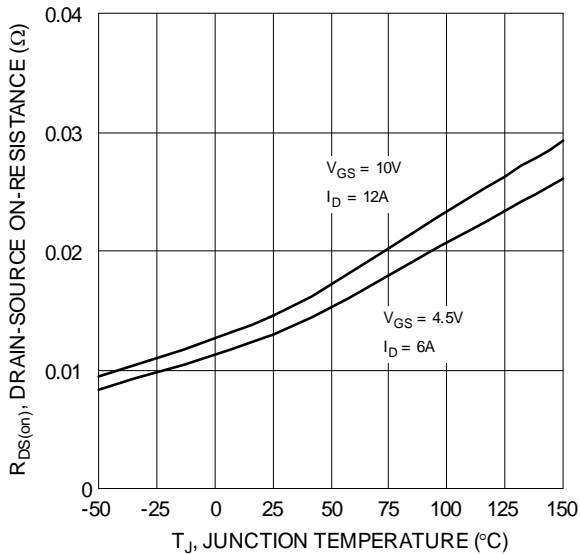
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	49	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	P_D	83.3	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	1.8	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

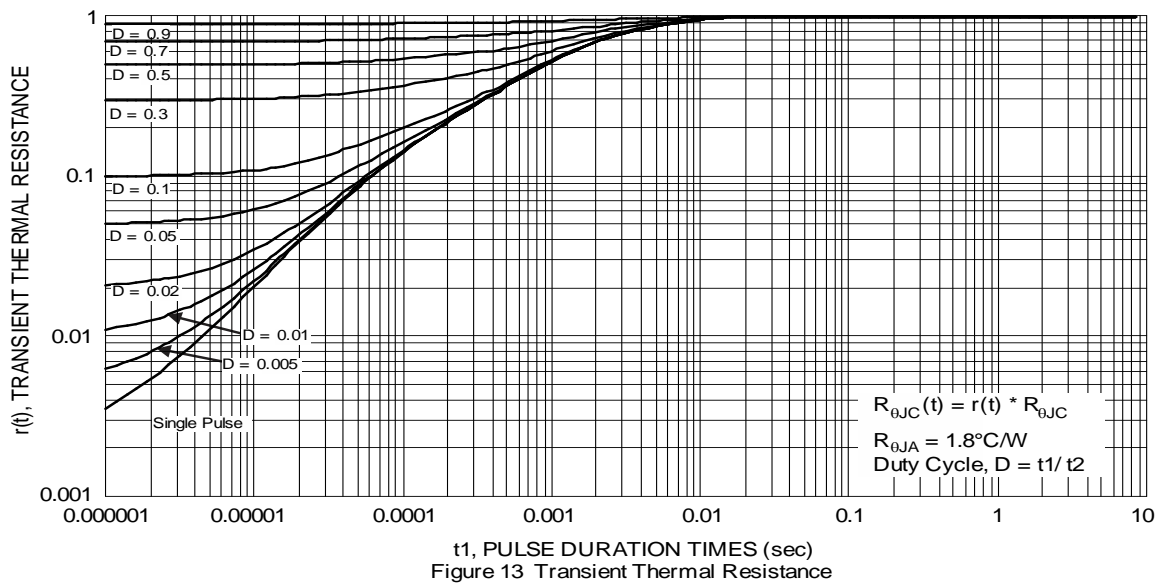
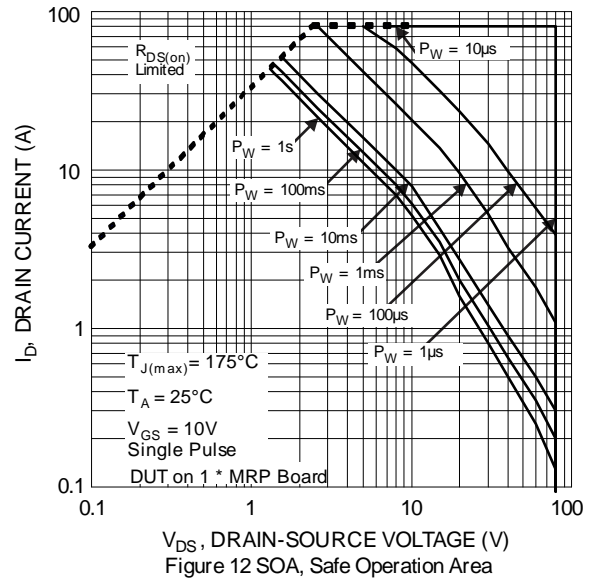
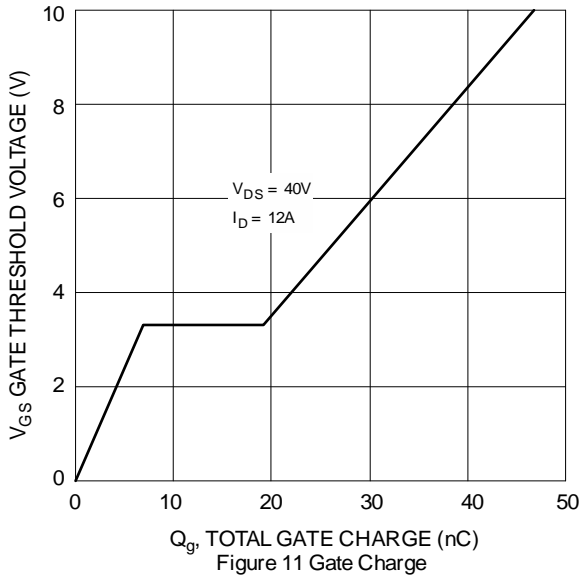
Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	80	-	-	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	μA	$V_{DS} = 64\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	-	3	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	14	17	m Ω	$V_{GS} = 10\text{V}, I_D = 12\text{A}$
		-	16.5	23.5		$V_{GS} = 4.5\text{V}, I_D = 6\text{A}$
Diode Forward Voltage	V_{SD}	-	0.9	1.2	V	$V_{GS} = 0\text{V}, I_S = 20\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	1949	-	pF	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}	-	177	-		
Reverse Transfer Capacitance	C_{rss}	-	10	-		
Gate Resistance	R_g	-	0.7	-	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	-	15	-	nC	$V_{DS} = 40\text{V}, I_D = 12\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	-	34	-		
Gate-Source Charge	Q_{gs}	-	6	-		
Gate-Drain Charge	Q_{gd}	-	4.5	-		
Turn-On Delay Time	$t_{D(ON)}$	-	4.9	-	ns	$V_{DD} = 40\text{V}, V_{GS} = 10\text{V}, I_D = 12\text{A}, R_g = 1.6\Omega$
Turn-On Rise Time	t_R	-	3.8	-		
Turn-Off Delay Time	$t_{D(OFF)}$	-	16.5	-		
Turn-Off Fall Time	t_F	-	3.5	-		
Body Diode Reverse Recovery Time	t_{RR}	-	30.2	-	ns	$I_F = 12\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	-	34.6	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



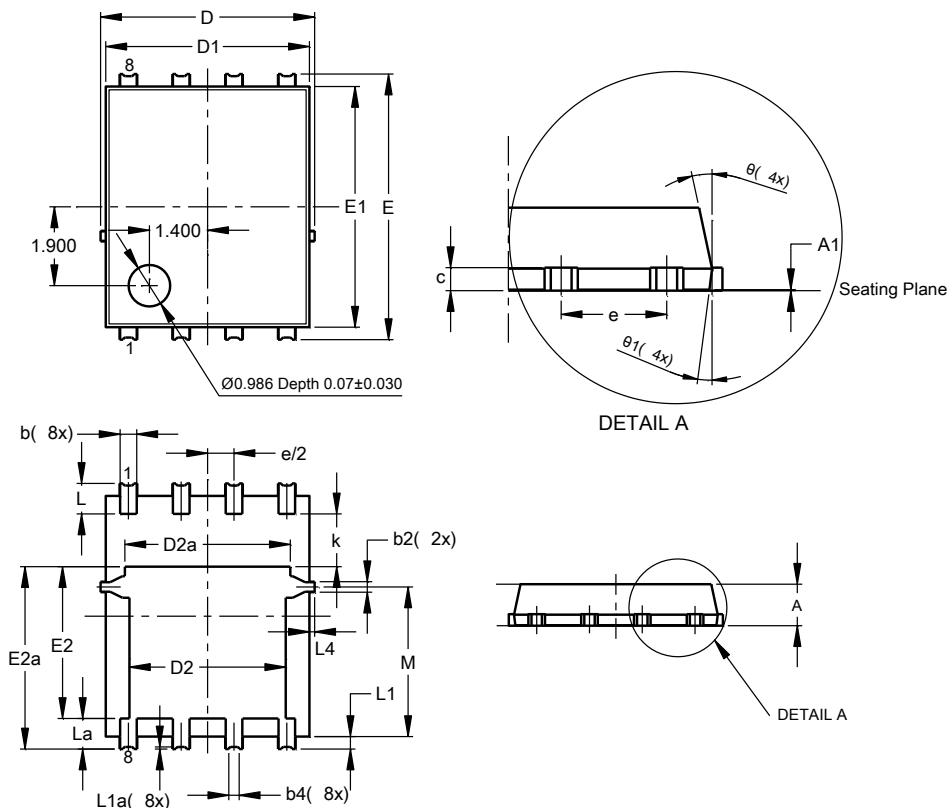




Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (SWP) (Type Q)

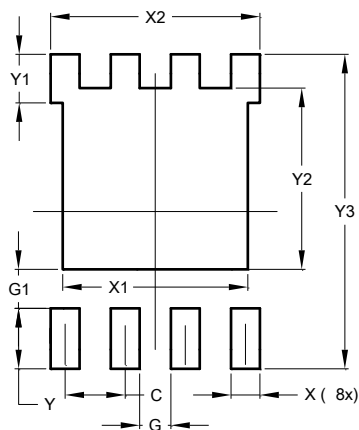


PowerDI5060-8 (SWP) (Type Q)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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